Diode Semiconductor Device - Page 1 of 1



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| Gla | ISS |
|------|--|
| Ove | erall Length: |
| 0.1 | 05 inches |
| Ter | minal Length: |
| 1.0 | 00 inches |
| Ove | erall Diameter: |
| 0.1 | 45 inches |
| Мо | unting Method: |
| Ter | minal |
| Fea | atures Provided: |
| Her | rmetically sealed case |
| Ser | miconductor Material: |
| Sili | con |
| Vol | tage Rating In Volts Per Characteristic: |
| 100 | 0.0 reverse voltage, peak |
| Cu | rrent Rating Per Characteristic: |
| 3.0 | 0 amperes source cutoff current preset |
| Ma | ximum Operating Tempurature Per Measurement Point: |
| 175 | 5.0 degrees celsius ambient air |
| Ter | minal Type And Quantity: |
| 2 u | ninsulated wire lead |
| She | elf Life: |
| N/a | l |
| Uni | it Of Measure: |
| | |
| Dei | militarization: |
| No | |
| Fiig | g: |
| A11 | 10a0 |